

# ANTREX Electronics

## Electronic Components Sourcing Information

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### Product Reference Information

|                      |                           |
|----------------------|---------------------------|
| <b>Part Number:</b>  | PSMNR67-30YLEX            |
| <b>Manufacturer:</b> | Nexperia USA Inc.         |
| <b>Package:</b>      | Please confirm with sales |
| <b>Availability:</b> | Please confirm with sales |

#### Product Page:

<https://antrexco.com/product/details/nexperia-usa-inc/psmnr67-30ylex.html>

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#### Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.



# PSMNR67-30YLE

N-channel 30 V, 0.70 mOhm, ASFET for hotswap with enhanced SOA in LPAK56E

10 November 2022

Product data sheet

## 1. General description

N-channel enhancement mode ASFET for hotswap with enhanced SOA in LPAK56E package optimized for low  $R_{DSon}$  and strong safe operating area, optimized for hot-swap, inrush and linear-mode applications.

## 2. Features and benefits

- Fully optimized Safe Operating Area (SOA) for superior linear mode operation
- Optimized for low  $R_{DSon}$  / low  $I^2R$  conduction losses
- LPAK56E package for applications that demand the highest performance and reliability in a 30 mm<sup>2</sup> footprint
- Low leakage <1  $\mu$ A at 25 °C
- Copper-clip for low parasitic inductance and resistance
- High reliability LPAK package, qualified to 175 °C

## 3. Applications

- Hot swap in 12 V-20 V applications
- e-Fuse
- DC switch
- Load switch
- Battery protection

## 4. Quick reference data

Table 1. Quick reference data

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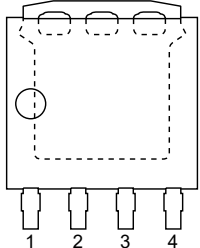
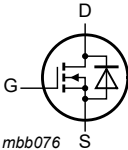
| Symbol                  | Parameter                        | Conditions                                                                                                                                        |     | Min | Typ  | Max | Unit |
|-------------------------|----------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|------|-----|------|
| V <sub>DS</sub>         | drain-source voltage             | 25 °C ≤ T <sub>J</sub> ≤ 175 °C                                                                                                                   |     | -   | -    | 30  | V    |
| I <sub>D</sub>          | drain current                    | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>                                                                           | [1] | -   | -    | 365 | A    |
| P <sub>tot</sub>        | total power dissipation          | T <sub>mb</sub> = 25 °C; <a href="#">Fig. 1</a>                                                                                                   |     | -   | -    | 333 | W    |
| T <sub>J</sub>          | junction temperature             |                                                                                                                                                   |     | -55 | -    | 175 | °C   |
| Static characteristics  |                                  |                                                                                                                                                   |     |     |      |     |      |
| R <sub>DSon</sub>       | drain-source on-state resistance | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 25 °C; <a href="#">Fig. 10</a>                                                    |     | -   | 0.64 | 0.7 | mΩ   |
|                         |                                  | V <sub>GS</sub> = 7 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 25 °C; <a href="#">Fig. 10</a>                                                     |     | -   | 0.75 | 1   | mΩ   |
| Dynamic characteristics |                                  |                                                                                                                                                   |     |     |      |     |      |
| Q <sub>GD</sub>         | gate-drain charge                | I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V; T <sub>J</sub> = 25 °C; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a> |     | 2   | 13   | 26  | nC   |
| Q <sub>G(tot)</sub>     | total gate charge                |                                                                                                                                                   |     | 23  | 52   | 86  | nC   |

| Symbol                    | Parameter       | Conditions                                                                                                                                                                | Min | Typ  | Max | Unit |
|---------------------------|-----------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|------|-----|------|
| <b>Source-drain diode</b> |                 |                                                                                                                                                                           |     |      |     |      |
| S                         | softness factor | $I_S = 25\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 15\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 16</a> | -   | 0.94 | -   |      |

[1] 365 A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline                                                                                                    | Graphic symbol                                                                                    |
|-----|--------|-----------------------------------|-----------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------|
| 1   | S      | source                            |  <p>LPAK56E; Power-SO8 (SOT1023)</p> |  <p>mbb076</p> |
| 2   | S      | source                            |                                                                                                                       |                                                                                                   |
| 3   | S      | source                            |                                                                                                                       |                                                                                                   |
| 4   | G      | gate                              |                                                                                                                       |                                                                                                   |
| mb  | D      | mounting base; connected to drain |                                                                                                                       |                                                                                                   |

## 6. Ordering information

Table 3. Ordering information

| Type number   | Package            |                                                                                |         |
|---------------|--------------------|--------------------------------------------------------------------------------|---------|
|               | Name               | Description                                                                    | Version |
| PSMNR67-30YLE | LPAK56E; Power-SO8 | plastic, single-ended surface-mounted package (LPAK56); 4 leads; 1.27 mm pitch | SOT1023 |

## 7. Marking

Table 4. Marking codes

| Type number   | Marking code |
|---------------|--------------|
| PSMNR67-30YLE | E67L30J      |

## 8. Limiting values

Table 5. Limiting values

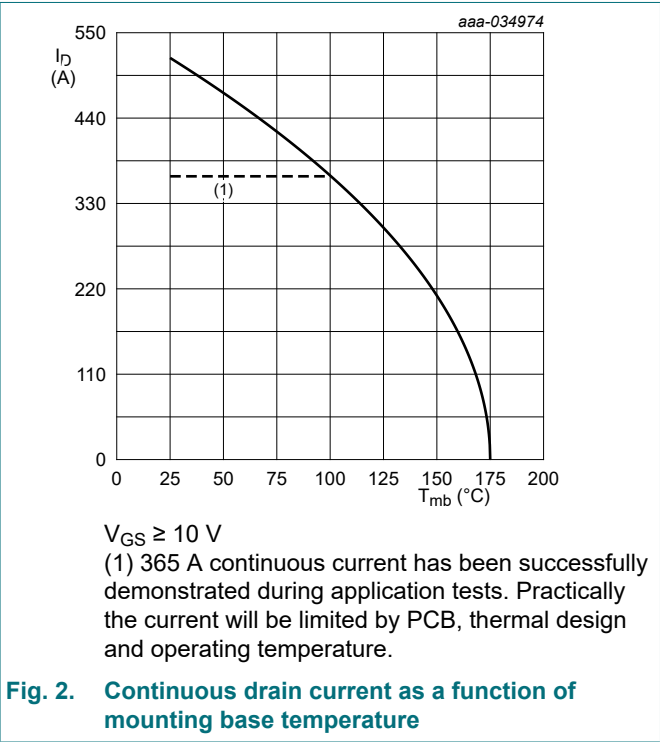
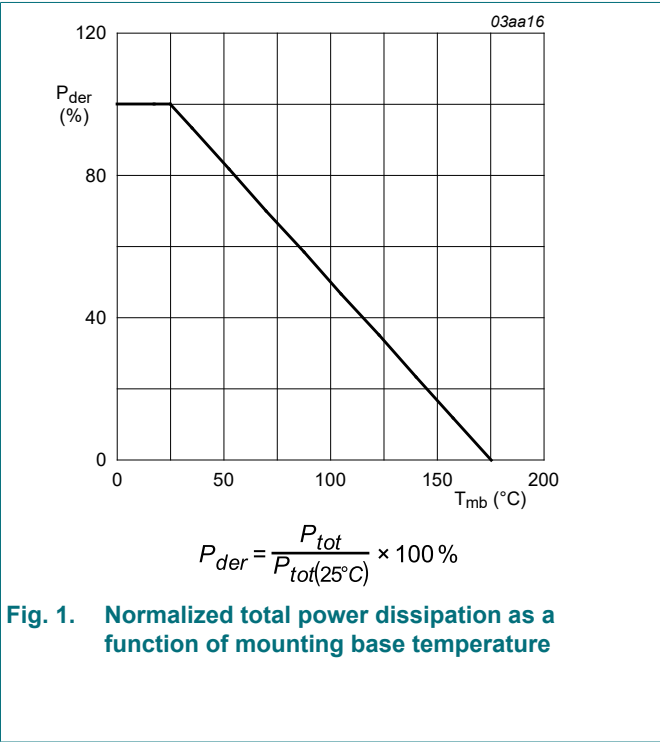
In accordance with the Absolute Maximum Rating System (IEC 60134).  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise stated.

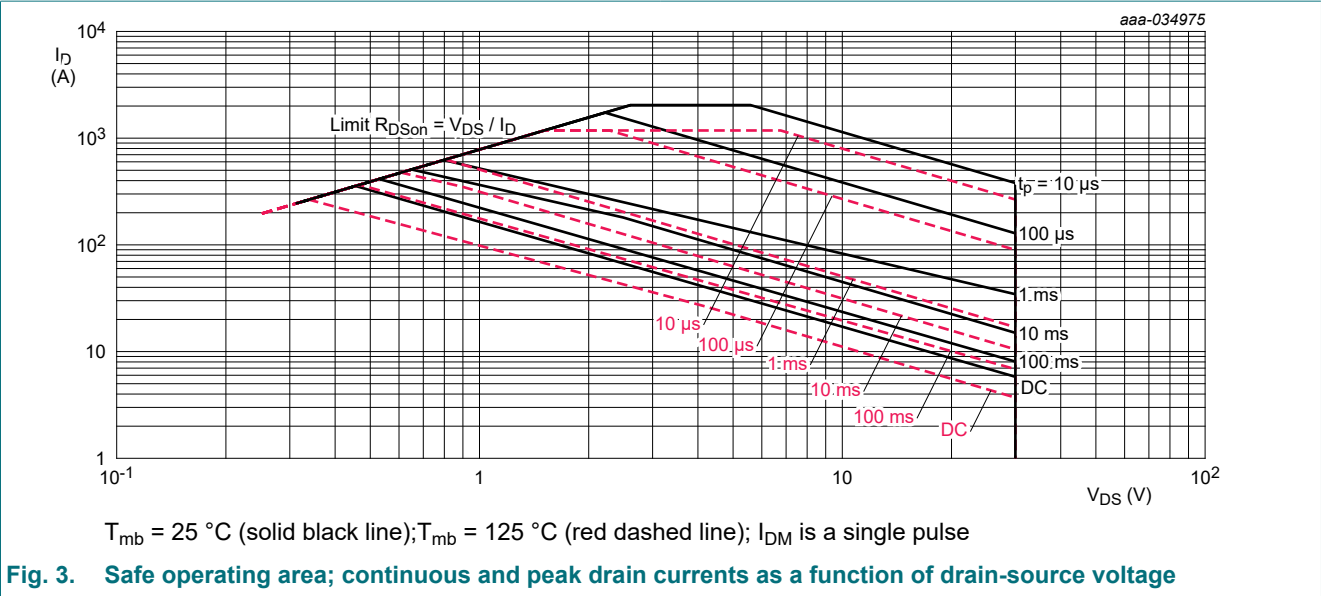
| Symbol    | Parameter               | Conditions                                                                                              | Min | Max  | Unit |
|-----------|-------------------------|---------------------------------------------------------------------------------------------------------|-----|------|------|
| $V_{DS}$  | drain-source voltage    | $25\text{ }^\circ\text{C} \leq T_J \leq 175\text{ }^\circ\text{C}$                                      | -   | 30   | V    |
| $V_{DGR}$ | drain-gate voltage      | $25\text{ }^\circ\text{C} \leq T_J \leq 175\text{ }^\circ\text{C}$ ; $R_{GS} = 20\text{ k}\Omega$       | -   | 30   | V    |
| $V_{GS}$  | gate-source voltage     |                                                                                                         | -20 | 20   | V    |
| $P_{tot}$ | total power dissipation | $T_{mb} = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a>                                            | -   | 333  | W    |
| $I_D$     | drain current           | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 2</a>                   | [1] | 365  | A    |
|           |                         | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ }^\circ\text{C}$ ; <a href="#">Fig. 2</a>                  | -   | 361  | A    |
| $I_{DM}$  | peak drain current      | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 3</a> | -   | 2070 | A    |

N-channel 30 V, 0.70 mOhm, ASFET for hotswap with enhanced SOA in LPAK56E

| Symbol               | Parameter                                    | Conditions                                                                                                                                                      |     | Min | Max  | Unit |
|----------------------|----------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|------|------|
| T <sub>stg</sub>     | storage temperature                          |                                                                                                                                                                 |     | -55 | 175  | °C   |
| T <sub>j</sub>       | junction temperature                         |                                                                                                                                                                 |     | -55 | 175  | °C   |
| T <sub>slid(M)</sub> | peak soldering temperature                   |                                                                                                                                                                 |     | -   | 260  | °C   |
| Source-drain diode   |                                              |                                                                                                                                                                 |     |     |      |      |
| I <sub>S</sub>       | source current                               | T <sub>mb</sub> = 25 °C                                                                                                                                         |     | -   | 333  | A    |
| I <sub>SM</sub>      | peak source current                          | pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C                                                                                                         |     | -   | 2070 | A    |
| Avalanche ruggedness |                                              |                                                                                                                                                                 |     |     |      |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | I <sub>D</sub> = 25 A; V <sub>sup</sub> ≤ 30 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped; t <sub>p</sub> = 10 ms | [2] | -   | 4.9  | J    |
| I <sub>AS</sub>      | non-repetitive avalanche current             | V <sub>sup</sub> ≤ 30 V; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; R <sub>GS</sub> = 50 Ω                                                           | [2] | -   | 190  | A    |

- [1] 365 A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Protected by 100% test.

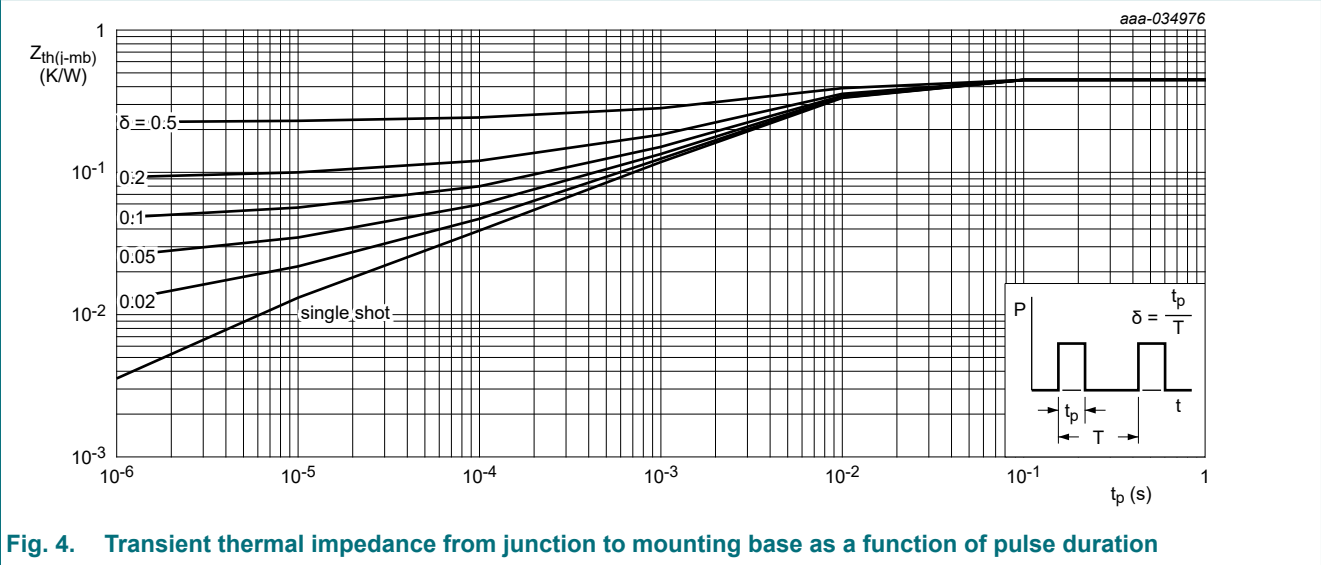


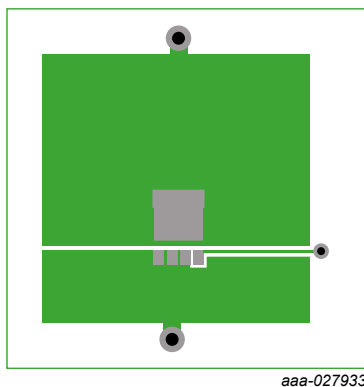


9. Thermal characteristics

Table 6. Thermal characteristics

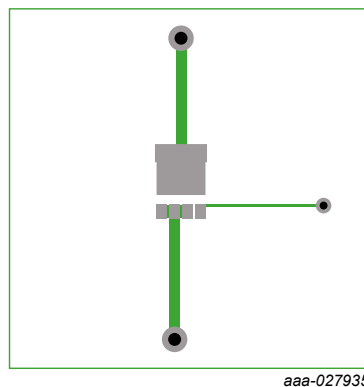
| Symbol         | Parameter                                         | Conditions | Min | Typ  | Max  | Unit |
|----------------|---------------------------------------------------|------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 4     | -   | 0.34 | 0.45 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | Fig. 5     | -   | 42   | -    | K/W  |
|                |                                                   | Fig. 6     | -   | 85   | -    | K/W  |





Copper area 25.4 mm square; 70 μm thick on FR4 board

**Fig. 5. PCB layout for thermal resistance from junction to ambient**



70 μm thick copper on FR4 board

**Fig. 6. PCB layout with minimum footprint for thermal resistance from junction to ambient**

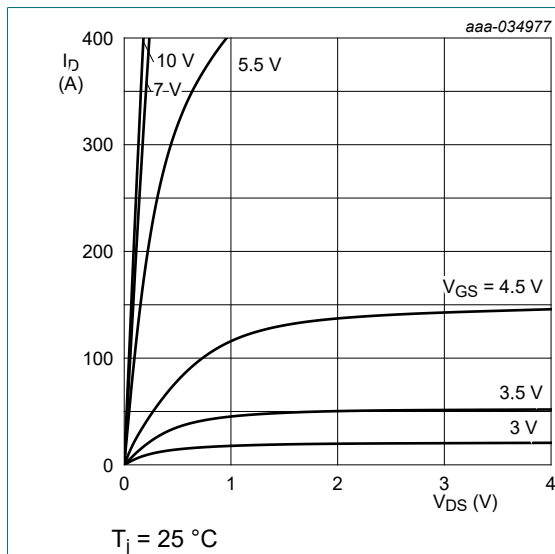
## 10. Characteristics

**Table 7. Characteristics**

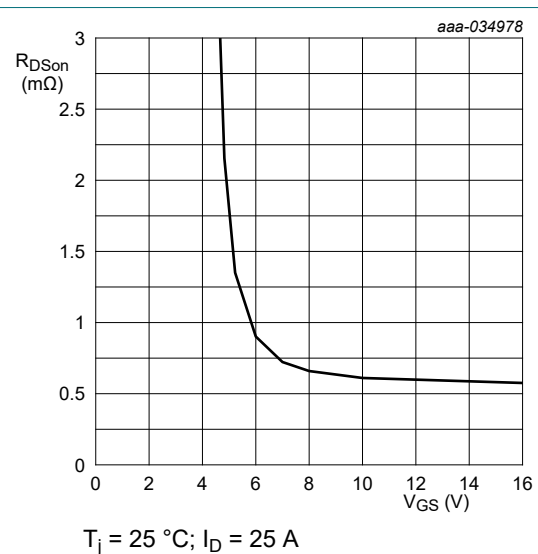
| Symbol                         | Parameter                                                | Conditions                                                                             | Min | Typ  | Max | Unit |
|--------------------------------|----------------------------------------------------------|----------------------------------------------------------------------------------------|-----|------|-----|------|
| <b>Static characteristics</b>  |                                                          |                                                                                        |     |      |     |      |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage                           | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25^\circ C$                                      | 30  | -    | -   | V    |
|                                |                                                          | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55^\circ C$                                     | 27  | -    | -   | V    |
| $V_{GS(th)}$                   | gate-source threshold voltage                            | $I_D = 2 mA; V_{DS} = V_{GS}; T_j = 25^\circ C$                                        | 1.2 | 1.79 | 2.2 | V    |
| $\Delta V_{GS(th)}/\Delta T$   | gate-source threshold voltage variation with temperature | $25^\circ C \leq T_j \leq 150^\circ C$                                                 | -   | -3.9 | -   | mV/K |
| $I_{DSS}$                      | drain leakage current                                    | $V_{DS} = 24 V; V_{GS} = 0 V; T_j = 25^\circ C$                                        | -   | -    | 1   | μA   |
|                                |                                                          | $V_{DS} = 24 V; V_{GS} = 0 V; T_j = 125^\circ C$                                       | -   | 10   | -   | μA   |
| $I_{GSS}$                      | gate leakage current                                     | $V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25^\circ C$                                        | -   | -    | 100 | nA   |
|                                |                                                          | $V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25^\circ C$                                       | -   | -    | 100 | nA   |
| $R_{DS(on)}$                   | drain-source on-state resistance                         | $V_{GS} = 10 V; I_D = 25 A; T_j = 25^\circ C; \text{Fig. 10}$                          | -   | 0.64 | 0.7 | mΩ   |
|                                |                                                          | $V_{GS} = 10 V; I_D = 25 A; T_j = 150^\circ C; \text{Fig. 11}$                         | -   | -    | 1.3 | mΩ   |
|                                |                                                          | $V_{GS} = 7 V; I_D = 25 A; T_j = 25^\circ C; \text{Fig. 10}$                           | -   | 0.75 | 1   | mΩ   |
|                                |                                                          | $V_{GS} = 7 V; I_D = 25 A; T_j = 150^\circ C; \text{Fig. 11}$                          | -   | -    | 1.9 | mΩ   |
| $R_G$                          | gate resistance                                          | $f = 1 MHz; T_j = 25^\circ C$                                                          | 1.4 | 3.6  | 9   | Ω    |
| <b>Dynamic characteristics</b> |                                                          |                                                                                        |     |      |     |      |
| $Q_{G(tot)}$                   | total gate charge                                        | $I_D = 25 A; V_{DS} = 15 V; V_{GS} = 4.5 V; T_j = 25^\circ C; \text{Fig. 12; Fig. 13}$ | 23  | 52   | 86  | nC   |
|                                |                                                          | $I_D = 25 A; V_{DS} = 15 V; V_{GS} = 10 V; T_j = 25^\circ C; \text{Fig. 12; Fig. 13}$  | 50  | 112  | 185 | nC   |
|                                |                                                          | $I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V; T_j = 25^\circ C$                             | -   | 60   | -   | nC   |

| Symbol                    | Parameter                         | Conditions                                                                                                                                                                   |     | Min  | Typ  | Max   | Unit |
|---------------------------|-----------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|------|------|-------|------|
| $Q_{GS}$                  | gate-source charge                | $I_D = 25\text{ A}$ ; $V_{DS} = 15\text{ V}$ ; $V_{GS} = 4.5\text{ V}$ ;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>             |     | 6.5  | 24   | 46    | nC   |
| $Q_{GS(th)}$              | pre-threshold gate-source charge  |                                                                                                                                                                              |     | 3.5  | 13   | 25    | nC   |
| $Q_{GS(th-pl)}$           | post-threshold gate-source charge |                                                                                                                                                                              |     | 3    | 11   | 21    | nC   |
| $Q_{GD}$                  | gate-drain charge                 |                                                                                                                                                                              |     | 2    | 13   | 26    | nC   |
| $V_{GS(pl)}$              | gate-source plateau voltage       | $I_D = 25\text{ A}$ ; $V_{DS} = 15\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>                                       |     | -    | 3.1  | -     | V    |
| $C_{iss}$                 | input capacitance                 | $V_{DS} = 15\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $f = 1\text{ MHz}$ ;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 14</a>                                          |     | 4967 | 8278 | 12417 | pF   |
| $C_{oss}$                 | output capacitance                |                                                                                                                                                                              |     | 1542 | 2570 | 3855  | pF   |
| $C_{rss}$                 | reverse transfer capacitance      |                                                                                                                                                                              |     | 117  | 435  | 1044  | pF   |
| $t_{d(on)}$               | turn-on delay time                | $V_{DS} = 15\text{ V}$ ; $R_L = 0.6\text{ }\Omega$ ; $V_{GS} = 4.5\text{ V}$ ;<br>$R_{G(ext)} = 5\text{ }\Omega$ ; $T_j = 25\text{ }^\circ\text{C}$                          |     | -    | 64   | -     | ns   |
| $t_r$                     | rise time                         |                                                                                                                                                                              |     | -    | 124  | -     | ns   |
| $t_{d(off)}$              | turn-off delay time               |                                                                                                                                                                              |     | -    | 52   | -     | ns   |
| $t_f$                     | fall time                         |                                                                                                                                                                              |     | -    | 59   | -     | ns   |
| $Q_{oss}$                 | output charge                     | $V_{GS} = 0\text{ V}$ ; $V_{DS} = 15\text{ V}$ ; $f = 1\text{ MHz}$ ;<br>$T_j = 25\text{ }^\circ\text{C}$                                                                    |     | -    | 62   | -     | nC   |
| <b>Source-drain diode</b> |                                   |                                                                                                                                                                              |     |      |      |       |      |
| $V_{SD}$                  | source-drain voltage              | $I_S = 25\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 15</a>                                                                     |     | -    | 0.77 | 1     | V    |
| $t_{rr}$                  | reverse recovery time             | $I_S = 25\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ;<br>$V_{DS} = 15\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 16</a> |     | -    | 42   | -     | ns   |
| $Q_r$                     | recovered charge                  |                                                                                                                                                                              | [1] | -    | 42   | -     | nC   |
| $t_a$                     | reverse recovery rise time        |                                                                                                                                                                              |     | -    | 21.5 | -     | ns   |
| $t_b$                     | reverse recovery fall time        |                                                                                                                                                                              |     | -    | 20.3 | -     | ns   |
| $S$                       | softness factor                   |                                                                                                                                                                              |     | -    | 0.94 | -     |      |

[1] includes capacitive recovery



**Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values**



**Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values**

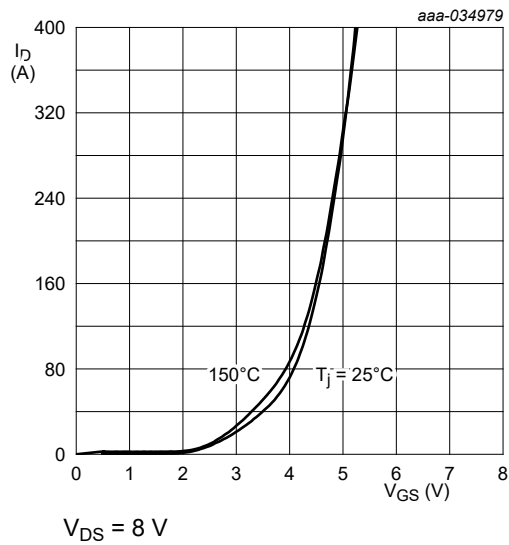


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

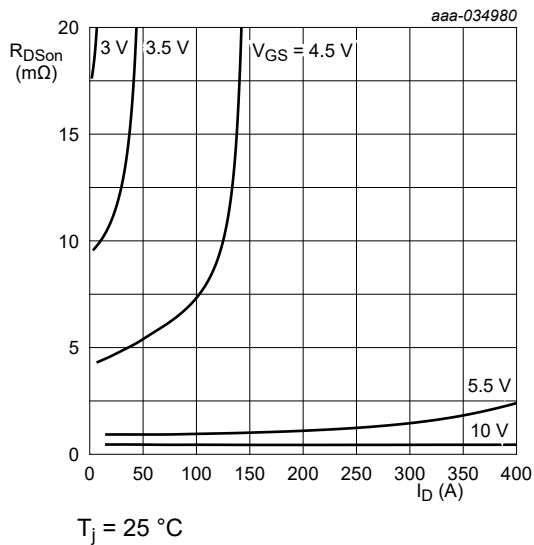


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

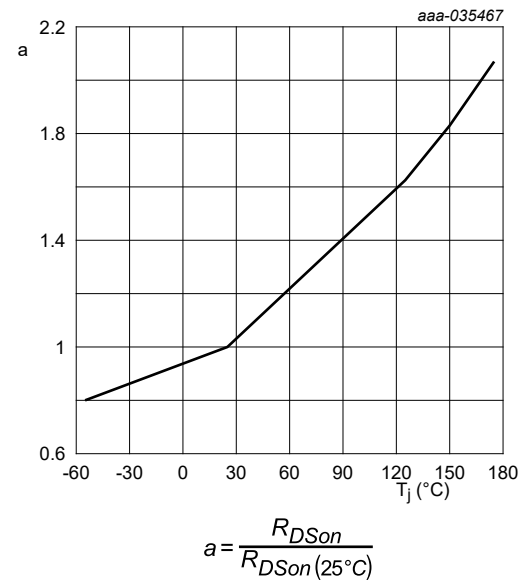


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

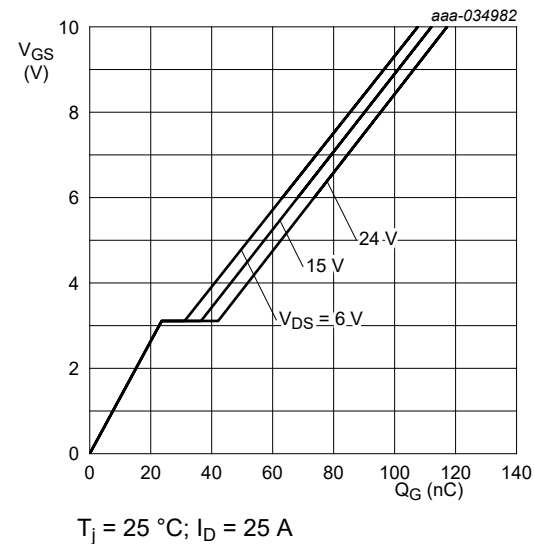


Fig. 12. Gate-source voltage as a function of gate charge; typical values

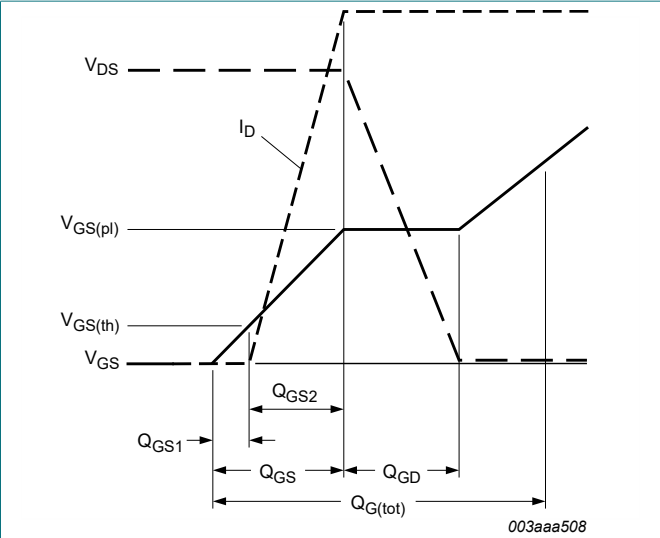


Fig. 13. Gate charge waveform definitions

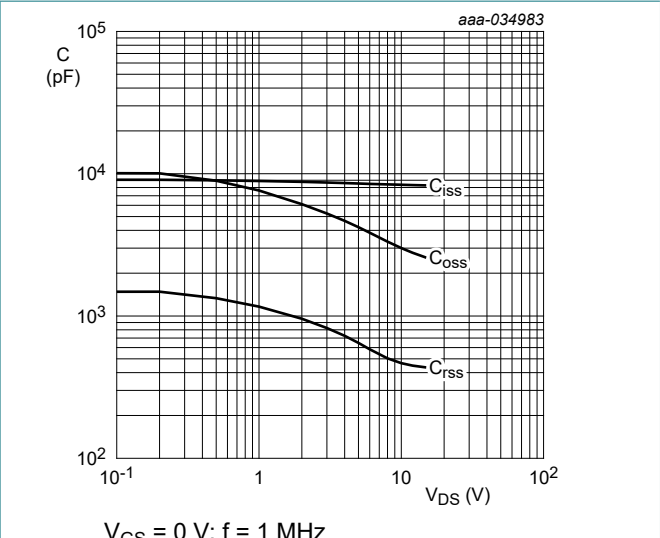


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

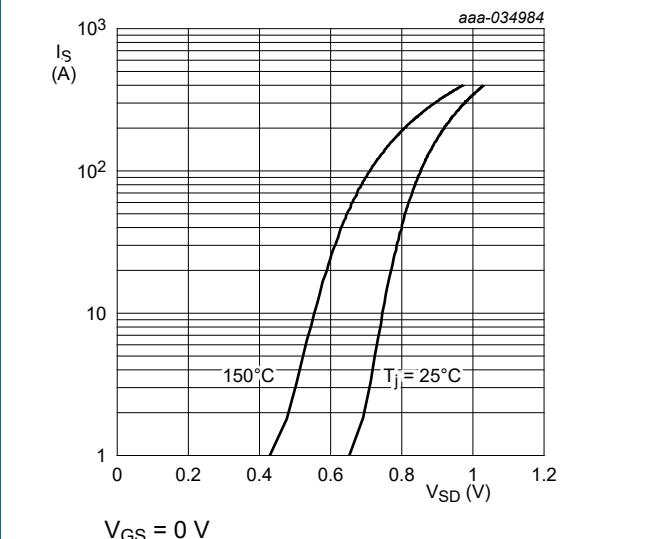


Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

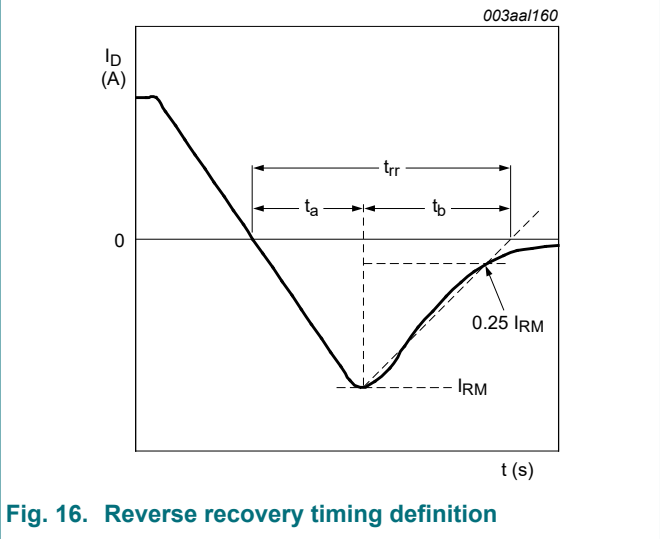
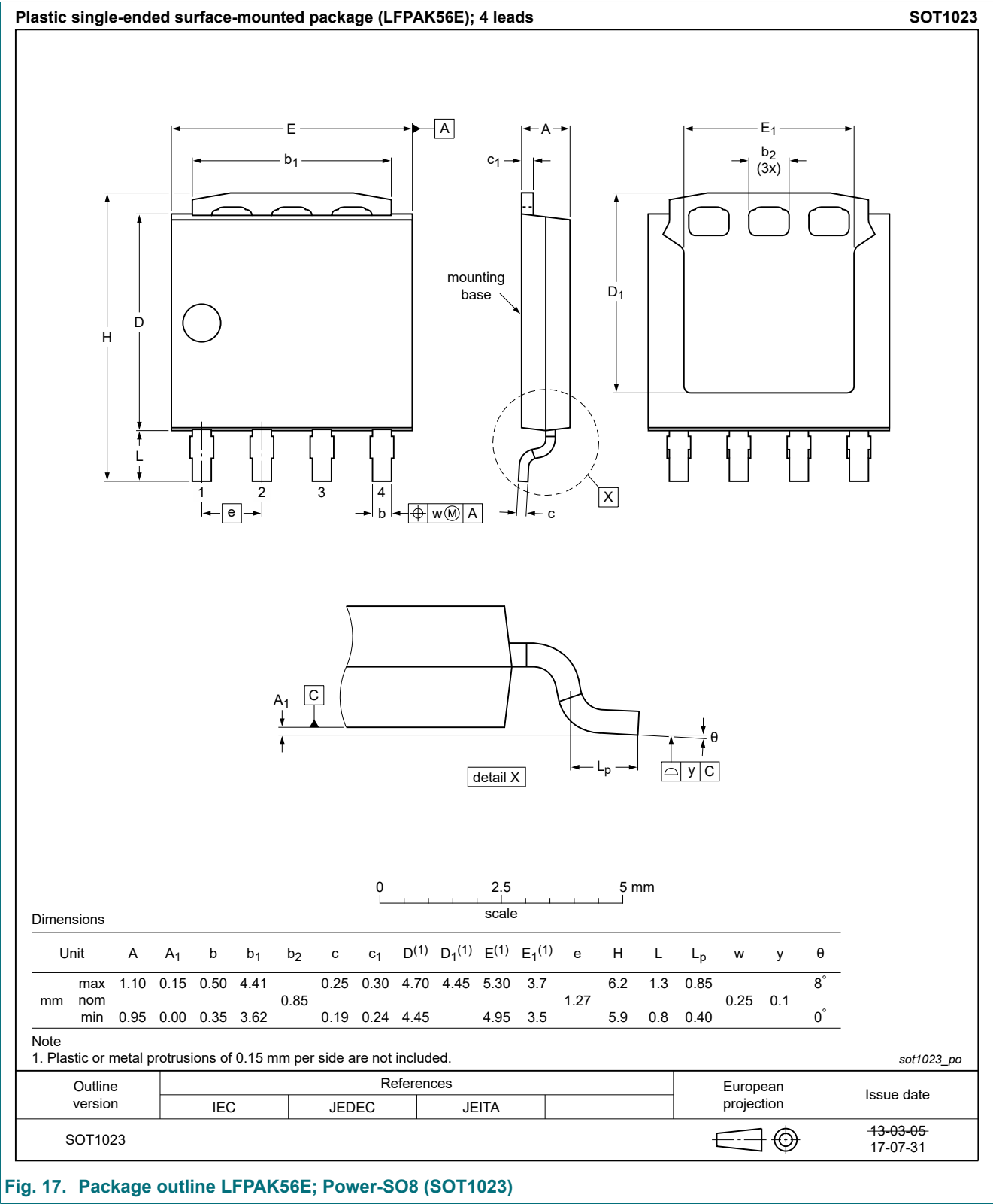
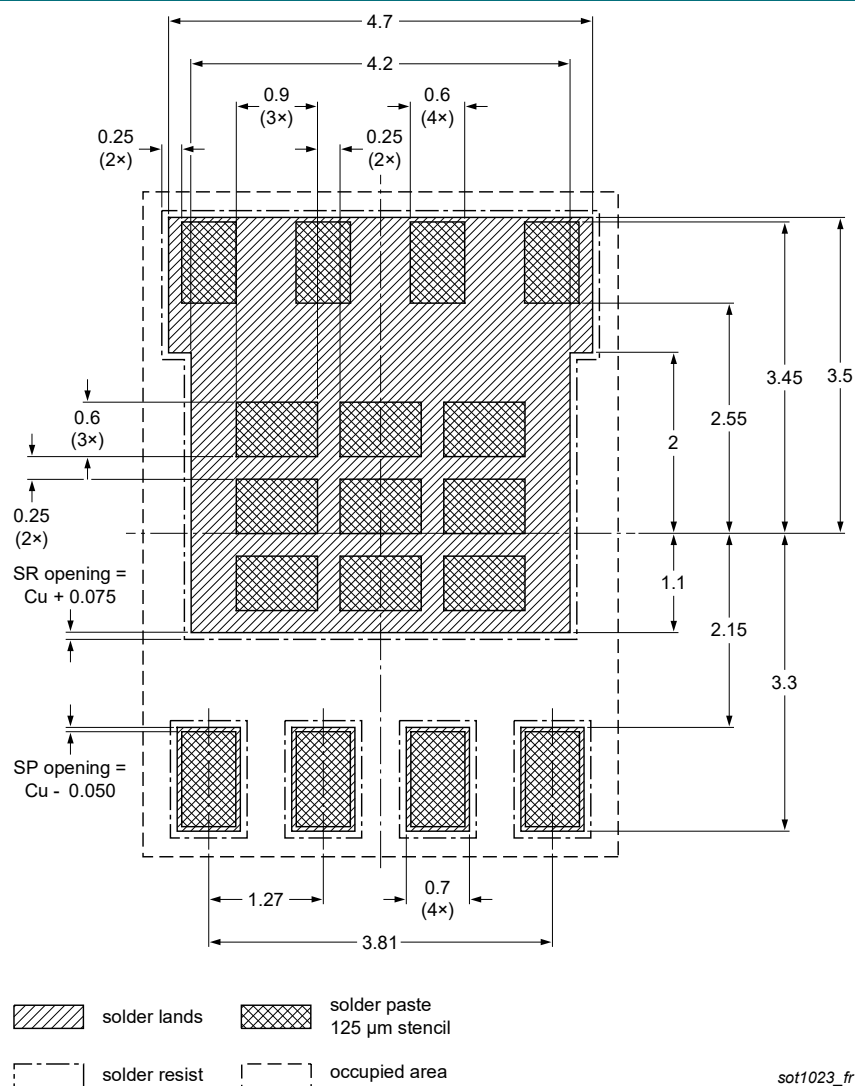


Fig. 16. Reverse recovery timing definition

11. Package outline



## 12. Soldering



**Fig. 18. Reflow soldering footprint for LPAK56E; Power-SO8 (SOT1023)**

## 13. Legal information

### Data sheet status

| Document status<br>[1][2]      | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <https://www.nexperia.com>.

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Date of release: 10 November 2022